

L Number	Hits	Search Text	DB	Time stamp
1	5617	semiconductor same device and diffusion and layer and pn same layer	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 07:33
2	2030	semiconductor same device and diffusion and layer and pn same layer and chip	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 07:33
3	608	semiconductor same device and diffusion and layer and pn same layer and single same chip	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 08:44
4	2	semiconductor same device and diffusion and layer and pn same layer and single same chip and analytic same circuit	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 08:33
5	55710	Takashi	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 08:33
6	55	semiconductor same device and diffusion and layer and pn same layer and a same ray and single same chip	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 08:50
8	34	semiconductor same device and diffusion and layer and pn same layer and detect same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 08:57
9	36	semiconductor same device and diffusion and layer and pn same junction and detect same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:01
11	36	semiconductor same device and diffusion and layer and pn same junction and detect same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 10:08
12	1055866	semiconductor diffusion and layer and "pn junction" and detect same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:03
13	1055865	semiconductor diffusion and layer and "pn junction" and detect same alpha same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:03
14	5	semiconductor and diffusion and layer and "pn junction" and detect same alpha same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:16
16	3	semiconductor and diffusion and layer and "pn junction" and detect same alpha same ray and electric same charge	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:19
17	19	semiconductor and diffusion and "pn junction" and detect same ray and electric same charge	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:22
18	50	semiconductor and diffusion and "pn junction" and detect same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:24
19	5	semiconductor and diffusion and "pn junction" and detect same alpha same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:41
20	213	257/225.cc1s.	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:47

21		547	250/370.01.ccls.	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 10:04
22		56	250/370.02.ccls.	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:48
23		1	257/225.ccls. and semiconductor and diffusion and "pn junction" and detect same alpha same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 10:07
24		1	257/225.ccls. and "pn junction" and detect same alpha same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:47
28		1	250/370.02.ccls. and semiconductor and diffusion and "pn junction" and detect same alpha same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:49
29		3	250/370.02.ccls. and semiconductor and diffusion and pn	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:49
30		1	250/370.05.ccls. and semiconductor and diffusion and "pn junction" and detect same alpha same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:49
38		1	250/390.01.ccls. and pn same junction	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 10:00
37		362	250/390.01.ccls.	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 10:00
39		1	257/225.ccls. and semiconductor and diffusion and alpha same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 10:04
41		3939	250/370\$	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 10:05
43		7	250/370\$ and diffusion and layer and alpha adj ray and electric same charge	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 10:06
44		13	250/370\$ and diffusion and layer and alpha adj ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 10:06
46		213	257/225.ccls.	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 10:07
-		8189226	JP "10260135"	USPAT; US-PGPUB; EPO; DERWENT	2004/10/15 10:20
-		8189224	JP "10260135" and Mitsubishi	USPAT; US-PGPUB; EPO; DERWENT	2004/10/15 10:21
-		79	250/370.05.ccls.	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:49
-		1	250/370.05.ccls. and diffusion same layer and isotope	USPAT; US-PGPUB; EPO; DERWENT	2004/10/15 15:30

-	1	250/390.01.ccls. and diffusion same layer and isotope	USPAT; US-PGPUB; EPO; DERWENT	2004/10/18 09:59
-	223	semiconductor same device and diffusion same layer and isotope	USPAT; US-PGPUB; EPO; DERWENT	2004/10/15 15:31
-	44	semiconductor same device and diffusion same layer and isotope and a same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/15 15:33
-	9	radiation and neutron and semiconductor same device and diffusion same layer and isotope and a same ray	USPAT; US-PGPUB; EPO; DERWENT	2004/10/15 15:34